

APTD1608F3C 1.6 x 0.8 mm Infrared Emitting Diode

DESCRIPTION

- F3 Made with Gallium Arsenide Infrared Emitting diodes

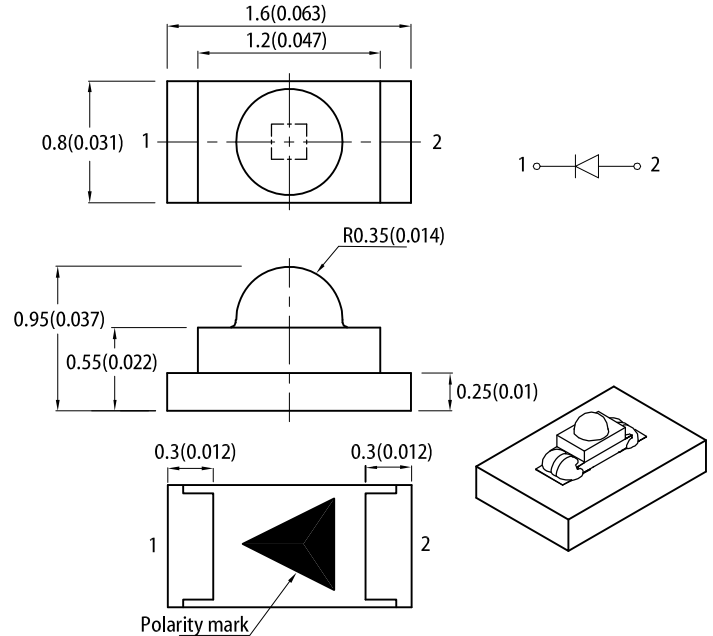
FEATURES

- 1.6 mm x 0.8 mm SMD LED, 0.95 mm thickness
- Low power consumption
- Mechanically and spectrally matched to phototransistor
- Package: 2000 pcs / reel
- Moisture sensitivity level: 3
- RoHS compliant

APPLICATIONS

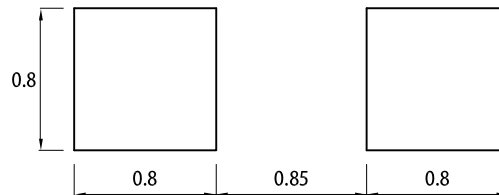
- Infrared Illumination for cameras
- Machine vision systems
- Surveillance systems
- Industrial electronics
- IR data transmission
- Remote control

PACKAGE DIMENSIONS



RECOMMENDED SOLDERING PATTERN

(units : mm; tolerance : ± 0.1)



Notes:

- All dimensions are in millimeters (inches).
- Tolerance is $\pm 0.15(0.006)$ unless otherwise noted.
- The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.
- The device has a single mounting surface. The device must be mounted according to the specifications.

SELECTION GUIDE

Part Number	Emitting Color (Material)	Lens Type	Po (mW/sr) @ 20mA ^[2]		Viewing Angle ^[1]
			Min.	Typ.	2θ1/2
APTD1608F3C	Infrared (GaAs)	Water Clear	2	5	120°
			*1.2	*3	

Notes:

1. $\theta 1/2$ is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value.

2. Radiant Intensity / luminous flux: +/-15%.

* Radiant intensity value is traceable to CIE127-2007 standards.

ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

Parameter	Symbol	Emitting Color	Value		Unit
			Typ.	Max.	
Wavelength at Peak Emission I _F = 20mA	λ _{peak}	Infrared	940	-	nm
Spectral Bandwidth at 50% Φ REL MAX I _F = 20mA	Δλ	Infrared	50	-	nm
Capacitance	C	Infrared	90	-	pF
Forward Voltage I _F = 20mA	V _F ^[1]	Infrared	1.2	1.6	V
Reverse Current (V _R = 5V)	I _R	Infrared	-	10	uA

Notes:

1. Forward voltage: ±0.1V.
2. Wavelength value is traceable to CIE127-2007 standards.
3. Excess driving current and / or operating temperature higher than recommended conditions may result in severe light degradation or premature failure.

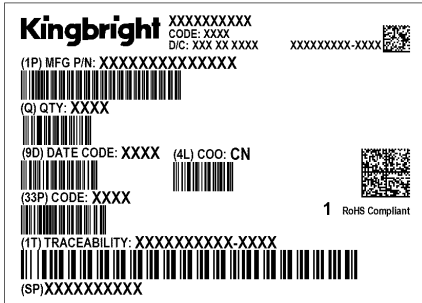
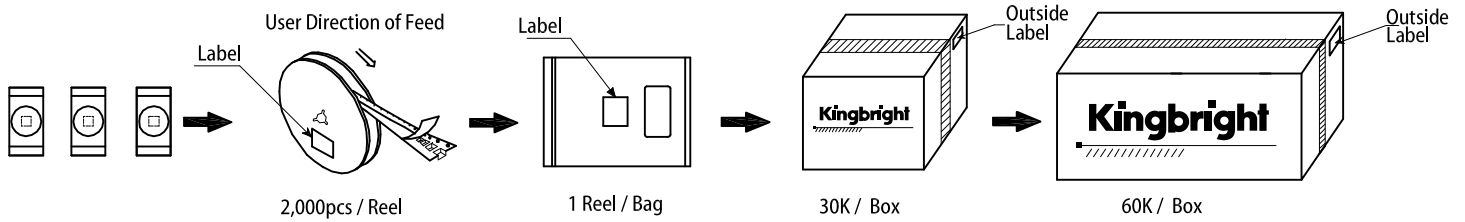
ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Symbol	Value	Unit
Power Dissipation	P _D	90	mW
Reverse Voltage	V _R	5	V
Junction Temperature	T _j	115	°C
Operating Temperature	T _{op}	-40 to +85	°C
Storage Temperature	T _{stg}	-40 to +85	°C
DC Forward Current	I _F	50	mA
Peak Forward Current	I _{FM} ^[1]	1200	mA
Electrostatic Discharge Threshold (HBM)	-	8000	V

Notes:

1. 1/100 Duty Cycle, 10μs Pulse Width.
2. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

PACKING & LABEL SPECIFICATIONS



PRECAUTIONARY NOTES

1. The information included in this document reflects representative usage scenarios and is intended for technical reference only.
2. The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
3. When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If customer usage exceeds the specified limits, Kingbright will not be responsible for any subsequent issues.
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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9